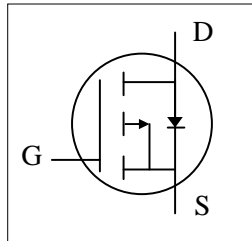




- ▼ Low Gate Charge
- ▼ Simple Drive Requirement
- ▼ Lower On-resistance
- ▼ RoHS Compliant & Halogen-Free

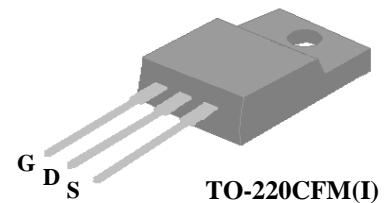


$BV_{DSS}$	-30V
$R_{DS(ON)}$	9m $\Omega$
$I_D$	-48A

### Description

AP6679 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-220CFM package is widely preferred for all commercial-industrial through hole applications. The mold compound provides a high isolation voltage capability and low thermal resistance between the tab and the external heat-sink.



### Absolute Maximum Ratings @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	+25	V
$I_D @ T_C=25^\circ\text{C}$	Drain Current, $V_{GS} @ 10\text{V}$	-48	A
$I_D @ T_C=100^\circ\text{C}$	Drain Current, $V_{GS} @ 10\text{V}$	-30	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	300	A
$P_D @ T_C=25^\circ\text{C}$	Total Power Dissipation	31.3	W
	Linear Derating Factor	0.25	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_j$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Value	Units
$R_{thj-c}$	Maximum Thermal Resistance, Junction-case	4	$^\circ\text{C}/\text{W}$
$R_{thj-a}$	Maximum Thermal Resistance, Junction-ambient	65	$^\circ\text{C}/\text{W}$



# AP6679GI-HF

## Electrical Characteristics @ $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^{\circ}\text{C}, I_D=-1\text{mA}$	-	-0.02	-	$V/^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-10V, I_D=-30A$	-	-	9	m $\Omega$
		$V_{GS}=-4.5V, I_D=-24A$	-	-	15	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-	-3	V
$g_{fs}$	Forward Transconductance	$V_{DS}=-10V, I_D=-30A$	-	43	-	S
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	$\mu A$
	Drain-Source Leakage Current ( $T_j=125^{\circ}\text{C}$ )	$V_{DS}=-24V, V_{GS}=0V$	-	-	-250	$\mu A$
$I_{GSS}$	Halogen-Free	$V_{GS}=+25, V_{DS}=0V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge	$I_D=-30A$	-	40	67	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=-25V$	-	8	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=-4.5V$	-	28	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=-15V$	-	15	-	ns
$t_r$	Rise Time	$I_D=-30A$	-	75	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=-10V$	-	50	-	ns
$t_f$	Fall Time	$R_D=0.5\Omega$	-	90	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	3100	4590	pF
$C_{oss}$	Output Capacitance	$V_{DS}=-25V$	-	930	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	690	-	pF
$R_g$	Gate Resistance	$f=1.0\text{MHz}$	-	2.7	4	$\Omega$

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$I_S=-30A, V_{GS}=0V$	-	-	-1.3	V
$t_{rr}$	Reverse Recovery Time	$I_S=-24A, V_{GS}=0V,$	-	47	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di/dt=-100A/\mu s$	-	45	-	nC

### Notes:

1. Pulse width limited Max. junction temperature.
2. Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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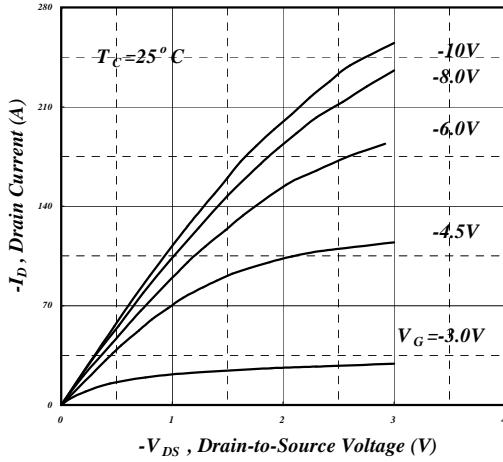


Fig 1. Typical Output Characteristics

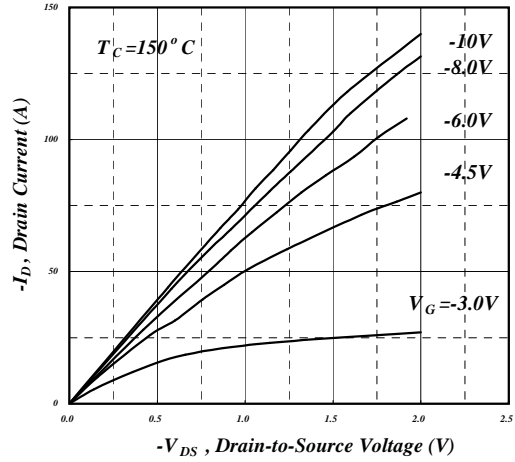


Fig 2. Typical Output Characteristics

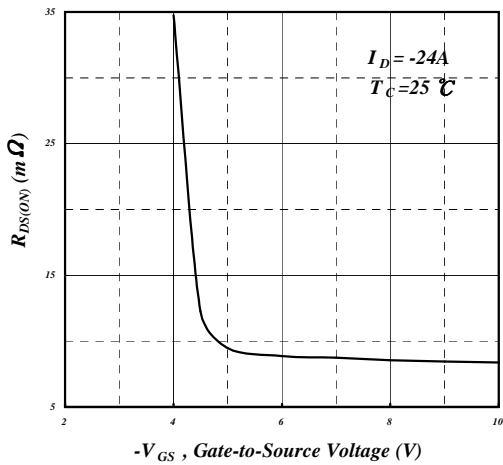


Fig 3. On-Resistance v.s. Gate Voltage

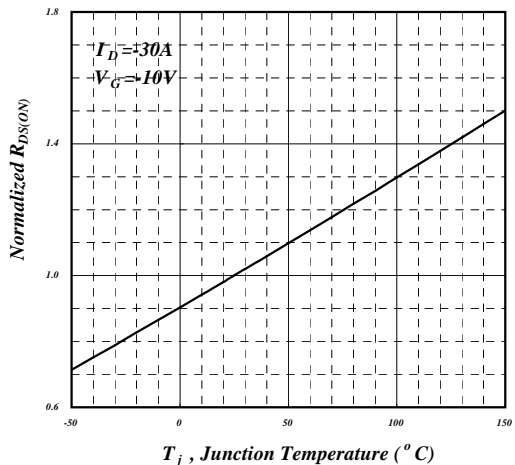


Fig 4. Normalized On-Resistance v.s. Junction Temperature

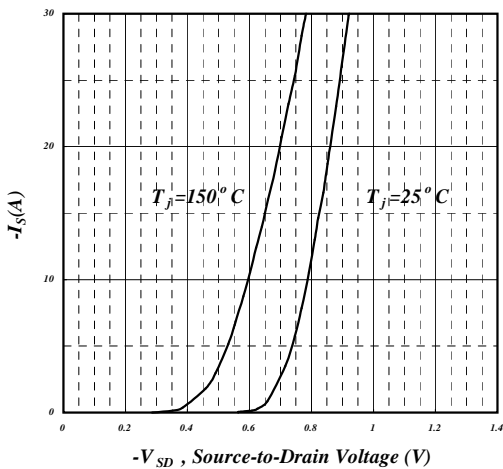


Fig 5. Forward Characteristic of Reverse Diode

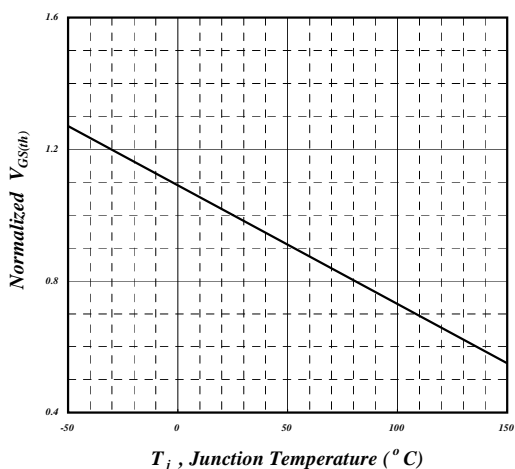


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

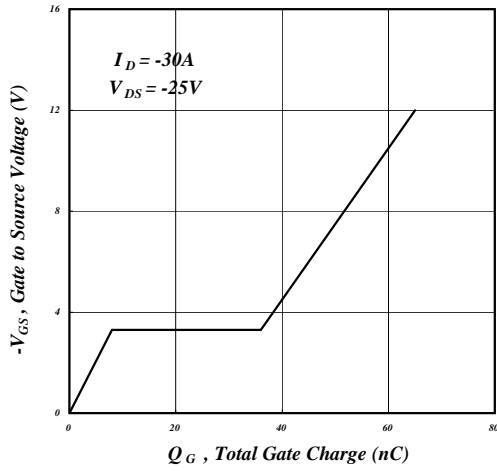


Fig 7. Gate Charge Characteristics

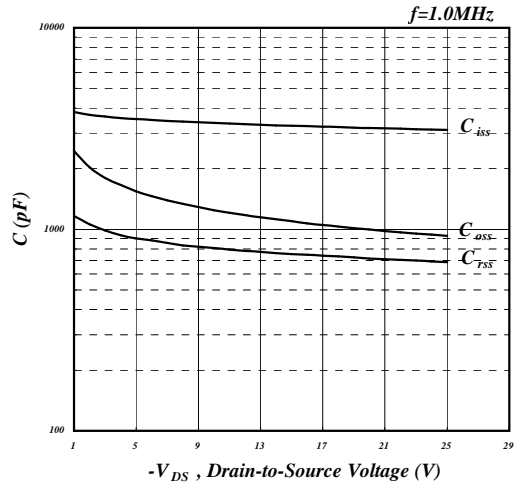


Fig 8. Typical Capacitance Characteristics

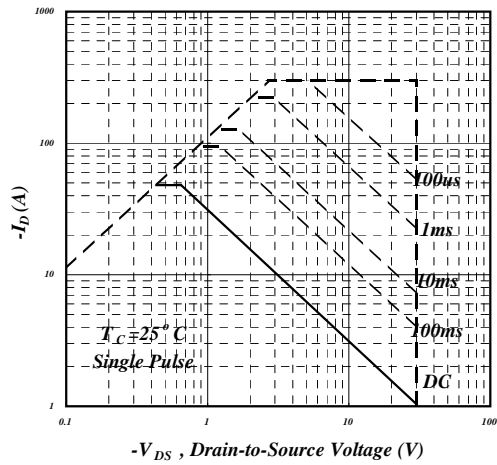


Fig 9. Maximum Safe Operating Area

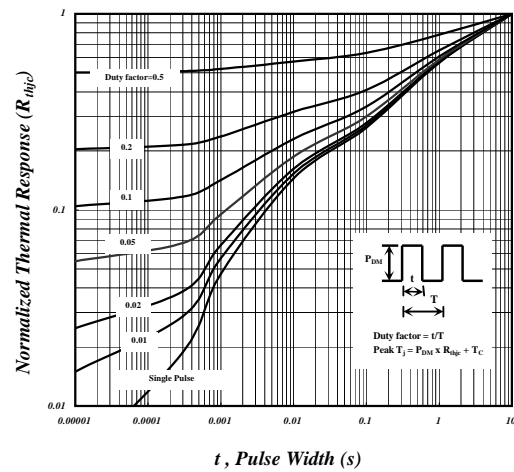


Fig 10. Effective Transient Thermal Impedance

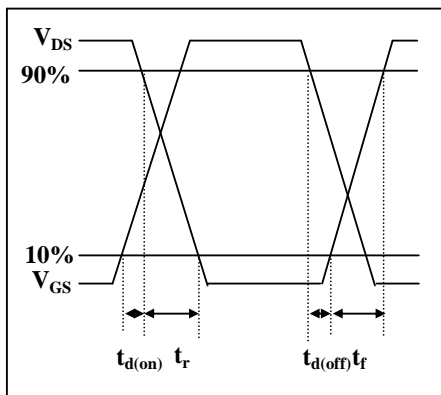


Fig 11. Switching Time Waveform

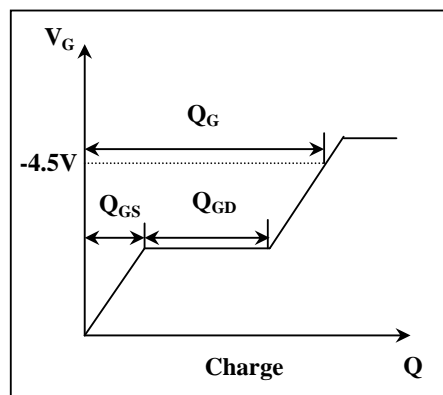


Fig 12. Gate Charge Waveform



# MARKING INFORMATION

